

Rapid Thermal Vacuum Process Oven with ramp up rate up to 150°C/K for wafer dia. 100 mm



(Picture similar -/ technical and design changes reserved)

- For single wafer up to 100mm (4")
- Ramp up rate up to 150°K/sec
- Control SIMATIC® with 7" touch panel
- Vacuum up to 10⁻⁶ hPa
- Process gas line with MFC for N₂

FEATURES

- Precise fast ramp up and fast ramp down rates
- Excellent temperature uniformity
- Up to 4 gas lines (MFC)
- Integrated data logging
- Heated by Infrared Lamps
- 50 programs with 50 steps each
- Small foot print

APPLICATION

- Implantation/Contact Annealing
- RTP, RTA, RTO, RTN
- Operation with inert gases, Oxygen, Hydrogen, Forming gas
- SiAu, SiAl, SiMo Alloying
- Low-k dielectrica

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- Crystallization & densification
- · Si-Solar Wafer Cells on glass by



- Rapid Thermal Annealing Process Oven with vacuum
- 7" Touch Panel
- Programmable temperature profiles
- Record of process data



The RTP-100 oven can be used for several different applications like annealing for silicon and compound semiconductor wafers (RTA), rapid thermal oxidation (RTO), rapid thermal nitridation (RTN), rapid thermal diffusion from spin-on dopant, crystallization, contact alloying and more.

PROCESS GASES

Beside standard process gases, like Nitrogen, Oxygen, Forming Gas the system (depends on model) can also be used with pure Hydrogen (Option: RTP-H2 and RTP-H2S). The chamber is sealed and can be easily cleaned.

GAS FLOW CONTROL

One gas line with Mass Flow Controller (MFC) for Nitrogen is default. Three more gas lines are possible(option:RTP-MFC).

VACUUM

The system is vacuum capable up to 10^{-6} hPa.

HEATING

The maximal achievable temperature is 1200 °C. Key features are precisely controlled fast ramp-up (up 150°K/sec) and excellent ramp-down rates (depend on temperature and loading).

TEMPERATURE

The RTP-100 allows an excellent temperature distribution and homogeneity. Optionally a graphite susceptor can be inserted into the quartz chamber (Option: GP Graphite Plate or Suszeptor).

PROGRAMMING

The RTP-100 is equipped with a 7" touch panel which allows easy and comfortable programming directly on the unit. 50 programs with 50 steps each can be stored. Unlimited programs can be upand downloaded from external storage medium.

PROCESS CONTROL

The software allows the permanent monitoring, read- out and analysis of



>temperature
>process gas flow
>cooling water level status
>pressure value and status

COOLING PROCESS

The cooling of the parts in the quartz chamber is realized by Nitrogen.

OTHERS

An interlock function as well as an Emergency-OFF-Button (EMO) are default.

SPECIAL

This oven can also be orderd as "double chamber oven". By adding a second process chamber (Option: PC-100) the oven does have 2 process chambers and one controller unit. This saves money when 2 different processes are needed and the chambers shall not be cleaned due to contamination or other reasons.



SPECIFICATION

Max. part size

Chamber material

Chamber height

Vacuum capability

Process chamber size

Temperature max.

Temp. unifomity

Heating

Ramp up rate

Ramp down rate

Flow Controller

Controller

Chamber cooling

Substrate Cooling

100 mm dia. (4")

Quartz glass muffle and quartz universal holder

18 mm

Up to 10⁻⁶ hPa

134 x 169 x 18 mm (W x D x H)

1200°C

 \leq ± 1,5% of set temperature

Top and bottom heating with 18 IR Lamps (20 kW)

Up to 150°K/sec (100 mm diameter Si wafer)

T = 1200°C > 400°C: 200 K/min, T = 400°C > 100°C: 30 K/min

Mass Flow Controller (Nitrogen 5 nlm)

SIMATIC®, 50 programs with 50 steps each

Water cooled

By Nitrogen Gas

TECHNICAL DATA

Dimension oven

Weight

Electrical connection

504 mm x 521 mm x 576 mm (W x D x H)

55 kg (estimated)

400/230V, 20kW



OPTIONS

RTP-H2 Hydrogen option with Safety device (Sensor and Hydrogen monitoring)

RTP-H2S Safety device for Hydrogen option (with cover and sensor)

RTP-MFC Additional process gas line with Mass Flow Controller (max. 3 add) *

* = all in all max. 4 process gas lines

RTP-Ox Oxygen Analyzer to measure Oxygen residues

(not in combination with Hydrogen Option)

RTP-MM Moisture Analyzer to measure moisture residues in the chamber

RTP-SW Switchbox for chiller and vacuum pump

RTP-TC add. Thermocouple to measure on device (plugged in chamber, max. 1)

RTP-VCR Tubing made of VCR (welded)

RTP-CAB Oven integrated as floor model into a cabinet with

Universal Heat Exchanger (UHE)

RTP-PYR Pyrometer on request

ACCESSORIES

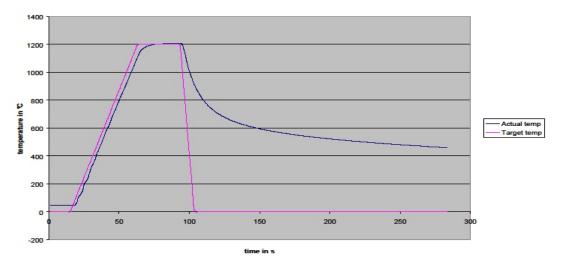
RTP-GP-100 Graphite Plate or susceptor (optional SiC coated)

RTP-PC-100 add. 100 mm oven chamber = double chamber(for usage of 2 chambers)

RTP-QR-50 Adapter (quartz ring) for 50 mm wafer **RTP-QR-75** Adapter (quartz ring) for 75 mm wafer

MP Membrane/diaphragm pump for vacuum up to 3 hPa RVP Rotary vane pump or dry pump for vacuum up to 10⁻³ hPa

RTP-1200-100 Anneal 1200 °C 15 s



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